



Product Summary

The ZM160P03D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

Advance high cell density Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

nd Synchronous Rectifier

Ratings $T_c = 25$

| Parameter | Symbol | Rating | Unit |
|---|-------------------------|------------|-------------|
| Drain-Source Voltage | V_{DS} | -30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | $I_{D@TC=25^{\circ}C}$ | -35 | A |
| | $I_{D@TC=75^{\circ}C}$ | -26 | A |
| | $I_{D@TC=100^{\circ}C}$ | -22 | A |
| Pulsed Drain Current ① | I_{DM} | -70 | A |
| Total Power Dissipation($TC=25^{\circ}C$) | $P_D@TC=25^{\circ}C$ | 55 | W |
| Total Power Dissipation($TA=25^{\circ}C$) | $P_D@TA=25^{\circ}C$ | 2.5 | W |
| Operating Junction Temperature | T_J | -55 to 150 | $^{\circ}C$ |
| Storage Temperature | T_{STG} | -55 to 150 | $^{\circ}C$ |
| Single Pulse Avalanche Energy | E_{AS} | 160 | mJ |



| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|--|-------------------|------|------|------|-------|
| Thermal resistance, junction - case | R _{thJC} | - | - | 2.1 | ° C/W |
| Thermal resistance, junction - ambient | R _{thJA} | - | - | 50 | ° C/W |
| Soldering temperature, wavesoldering for 10s | T _{sold} | - | - | 265 | |

